

Photodiode structures are grown by liquid phase epitaxy on InAs substrate. Schematic band diagram of standard PD structure with cut-off  $3.8 \,\mu\text{m}$  is schematically presented below. Spectral response is measured at room temperature and zero bias.  $3.8 \,\mu\text{m}$  cut-off is measured at 10% of the maximum responsivity.







Standard PD36 heterostructure

